

FORM PTO-878 Rev. 3-83 PATENT APPLICATION FEE DETERMINATION RECORD	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	SERIAL NO. 218 312	FILING DATE 7-12-88
		APPLICANT (PRINT NAME) Holmberg	

CLAIMS AS FILED - PART I

FOR	NO. FILED	NO. EXTRA
BASIC FEE		
TOTAL CLAIMS	36	16
INDEP. CLAIMS	4	1
MULTIPLE DEPENDENT CLAIMS PRESENT		

* If the difference in col. 1 is less than 20% enter "0" in col. 2

SMALL ENTITY

RATE	FEE
	\$170
x6	\$
x17	\$
x55	\$
TOTAL	\$

OTHER THAN A SMALL ENTITY

OR

RATE	FEE
	\$300
x12	\$192
x34	\$34
x110	\$
TOTAL	\$466

CLAIMS AS AMENDED - PART II

AMENDMENT A	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA
	TOTAL	MINUS	*
	INDEP.	MINUS	*
	FIRST PRESENTATION OF MULTIPLE DEP. CLAIMS		

SMALL ENTITY

RATE	ADDITIONAL FEE
\$	\$
15	\$
10	\$
TOTAL ADDITIONAL FEE	\$

OTHER THAN A SMALL ENTITY

OR

RATE	ADDITIONAL FEE
10	\$
10	\$
100	\$
TOTAL	\$

AMENDMENT B	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA
	TOTAL	MINUS	*
	INDEP.	MINUS	*
	FIRST PRESENTATION OF MULTIPLE DEP. CLAIMS		

RATE	ADDITIONAL FEE
\$	\$
15	\$
10	\$
TOTAL ADDITIONAL FEE	\$

OR

RATE	ADDITIONAL FEE
10	\$
10	\$
100	\$
TOTAL	\$

AMENDMENT C	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA
	TOTAL	MINUS	*
	INDEP.	MINUS	*
	FIRST PRESENTATION OF MULTIPLE DEP. CLAIMS		

RATE	ADDITIONAL FEE
\$	\$
15	\$
10	\$
TOTAL ADDITIONAL FEE	\$

OR

RATE	ADDITIONAL FEE
10	\$
10	\$
100	\$
TOTAL	\$

* If the entry in Col. 1 is less than the entry in Col. 2, enter "0" in Col. 3.
 ** If the Highest No. Previously Paid For in this SPACE is less than 25, enter "25".
 *** If the Highest No. Previously Paid For in this SPACE is less than 1, enter "1".
 The Highest No. Previously Paid For (Total or Indep.) is the highest number to use in the comparison test in Col. 1.

manufacture thereof; Karl J. Youtsey, et al.; ~~437691~~; 202*000, 002; 357*8;
427*122, 215, 220, 221, 228, 249, 255, 384, 385.5

23. 3,922,364, Nov. 25, 1975, Electrically conductive fibers; Thomas D.
Tadewald, 427*126.1; 65*3.47, 60.3; 427*185, 204; 428*032; ~~437323~~

24. 3,916,509, Nov. 4, 1975, Method of manufacturing a semi-conductor target
for a camera tube having a mosaic of p-n junctions covered by a perforated
conductive layer; Arthur Marie Eugene Hoeberechts, et al.; ~~43703~~; 357*56;

~~43705~~, 90, ~~441~~, ~~153~~, ~~916~~

25. 3,884,688, May 20, 1975, Photosensitive element employing a vitreous
bismuth-selenium film; John C. Schottmiller, et al., 428*457; 313*385;
430*84; ~~4376232~~, ~~916~~; 505*849

26. 3,874,917, Apr. 1, 1975, Method of forming vitreous semiconductors by
vapor depositing bismuth and selenium; Charles Wood, et al., ~~43753~~;
427*76, 160; 428*426, 446, 523; ~~4376232~~

=>

US PAT. NO. 4,791,071
US-CI-CURRENT: 437*42, 255, 238

ABSTRACT:

A . . . charge density and a higher dielectric breakdown strength, is
applicable to wide variety of MOSFET applications, and is inherently less
~~Electrostatic Discharge~~ (ESD) sensitive than conventional gate
structures due to the distributed electric field.

SUMMARY:

- 4,801,558, Jan. 31, 1987, Electrostatic discharge protection using thin nickel fuse; Arturo Simmons, et al., 4373170; 148*D16.55; 357*30; 43735, 22, 922
- 4,791,071, Dec. 13, 1988, Dual dielectric gate system comprising silicon dioxide and amorphous silicon; Saw T. Ang, 437342, 235, 238
- 5, 4,762,802, Aug. 9, 1988, Method for preventing latchup in CMOS devices; Louis C. Parrillo, 437324; 148*D16.82; 357*42, 91; 437326, 29, 34
- 5, 4,760,031, Jul. 26, 1988, Producing CCD imaging sensor with flashed backside metal film; James R. Janesick, 43733; 357*24; 437353, 181, 195, 203, 225
- 7, 4,624,862, Nov. 25, 1986, Boron doped semiconductor materials and method for producing same; Chi C. Yang, et al., 427*74; 136*258; 43732, 811, 208
- 8, 4,622,574, Nov. 11, 1986, Semiconductor chip with recessed bond pads; Enrique Garcia, 357*55, 56; 428*209; 4373204, 226
- 9, 4,586,242, May 6, 1986, Operations on a semiconductor integrated circuit having two kinds of buffers; Marc L. Harrison, 43738, 170
- 10, 4,574,466, Mar. 11, 1986, High quality gate oxides for VLSI devices; George F. Wagner, et al., 4373225; 148*D16.81, D16.118; 156*657; 427*255.4; 4373228
- 11, 4,534,099, Aug. 13, 1985, Method of making multilayer photoelectrodes and photovoltaic cells; Arthur T. Howe, 43732; 148*D16.20, D16.118; 357*67, 71; 427*74; 4373180, 181, 190, 192, 200
- 12, 4,520,010, May 28, 1985, Process for modifying the electrical properties of selenium, and selenium alloys; Santokh S. Badesha, et al., 4373232; 75*121; 423*508, 510; 427*74, 207.1
- 13, 4,471,369, Sep. 11, 1984, Robotic pressure imagers; Thomas R. Anthony, et al., 357*26; 73*862.04; 357*51, 55; 4373904
- 14, 4,463,216, Jul. 31, 1984, Solar cell; Hirotaka Nakano, et al., 136*256; 357*30, 32, 54; 43732, 236
- 15, 4,455,739, Jun. 26, 1984, Process protection for individual device gates on large area MIS devices; Jaroslav Hynecsek, 4373170, 8, 205, 226
- 16, 4,370,175, Jan. 25, 1983, Method of annealing implanted semiconductors by lasers; Jeffrey I. Levatter, 43732; 148*D16.90, D16.92, D16.93; 219*121.6; 357*30, 91; 427*53.1; 437319, 22, 236, 249
- 17, 4,359,512, Nov. 16, 1982, Layered photoconductive member having barrier of silicon and halogen; Tadaji Fukuda, et al., 430*57, 58, 65, 130, 132, 900; 43734
- 18, 4,234,361, Nov. 18, 1980, Process for producing an electrostatically deformable thin silicon membranes utilizing a two-stage diffusion step to form an etchant resistant layer; Henry Guckel, et al., 4373166; 29*621.1; 156*628, 648, 657, 662, 338*2, 4; 357*4, 26, 55, 60; 4373228
- 19, 4,225,222, Sep. 30, 1980, Printing drum for an electrostatic imaging process with a doped amorphous silicon layer; Karl Kempter, 353*3DR; 427*39; 430*57, 95, 133, 135, 136; 4373101
- 20, 4,139,935, Feb. 20, 1979, Over voltage protective device and circuits for insulated gate transistors; Claude L. Bertin, et al., 437312; 357*13, 23.13, 41, 91; 437340, 60, 165
- 21, 4,102,714, Jul. 25, 1978, Process for fabricating a low breakdown voltage device for polysilicon gate technology; David E. DeBar, et al., 437359, 148*D16.168; 156*653, 657, 662; 357*13, 23.9, 41, 55, 59, 60; 437399, 228, 204
- 22, 3,940,509, Feb. 24, 1976, Semi-conducting materials and a method for the